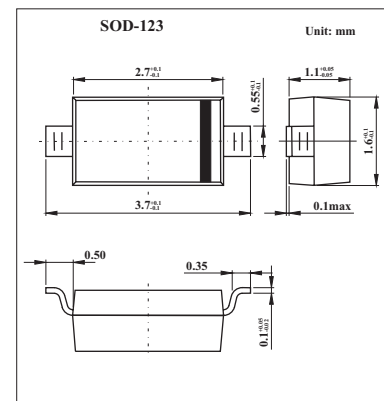


Silicon Epitaxial Planar Pin Diode

HVD142



■ Features

- Low capacitance. ($C = 0.35 \text{ pF max}$)
- Low forward resistance. ($r_f = 1.5 \ \Omega \text{ max}$)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 30 \text{ V}$			0.1	μA
Forward voltage	V_F	$I_F = 10 \text{ mA}$			1.0	V
Capacitance	C	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$			0.35	pF
Forward resistance	r_f	$I_F = 10 \text{ mA}, f = 100 \text{ MHz}$			1.5	Ω
ESD-Capability ^{*1}		$C = 200 \text{ pF}, R = 0 \ \Omega$, Both forward reverse direction 1 pulse.	100			V

Note

1. Failure criterion ; $I_R > 100 \text{ nA}$ at $V_R = 30 \text{ V}$

■ Marking

Marking	T2
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